

## Postdoctoral Position (MBE of GaSb integrated on Si PICs)

We are looking for a postdoctoral researcher on the molecular beam epitaxy (MBE) **growth of novel GaSb-based structures integrated on Silicon PICs with emission in the Mid-Infrared region**, as well as in the design, and characterization of the structures.

We offer a postdoctoral position for a highly motivated researcher with strong track-record, strongly committed to contribute to a breakthrough project in photonics.

The research will be carried out at the Nanophotonics Technology Center (<https://ntc.webs.upv.es/>) of the Universitat Politècnica de València, in collaboration with renowned partners. Research group (<https://ntc.webs.upv.es/iii-v-semiconductors-and-graphene/>)

Our research group belongs to the **Nanophotonics Technology Center (NTC) at Universitat Politècnica de València**.

### REQUIREMENTS:

- PhD in the epitaxial growth of III-V semiconductors by MBE.
- Full professional competence in English.
- Ability to work both independently and collaboratively.
- Degree in Physics, materials/telecommunication engineering, chemistry or similar.

### JOB CONDITIONS:

- Two-year contract (01/04/2024 – 31/03/2026); possibility of extension.
- Annual Gross Salary: 28,000 € - 32,000 €; commensurate with experience.
- Health and Social benefits included according to Spanish law.
- Work in a highly competitive international environment.
- Full access to a Unique Scientific and Technical Facility of the Spanish Government: ICTS MICRONANOFABS, NTC-UPV node (<https://micronanofabs.org/en/home-2/>)

Should you are interested, please **send us your CV and motivation letter:**

[vjgomher@ntc.upv.es](mailto:vjgomher@ntc.upv.es) and [misalas@ntc.upv.es](mailto:misalas@ntc.upv.es)

